UNITED STATES PATENT AND TRADEMARK OFFICE

CERTIFICATE OF CORRECTION

PATENT NO. : 7,142,577 B2
APPLICATION NO. : 09/855532
DATED : November 28, 2006
INVENTOR(S) : Joseph E. Geusic et al.

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On Title Page (Item 56)

In the Other Publications portion of References Cited, the following publication is added:

-- Yang, Peldong; Rizvi, A.H.; Messer, B.; Chmelka, B.F.; Whitesides, G.M.; Stucky, G.D., Patterning Porous Oxides within Microchannel Networks, Adv. Mater., 13(6) Mar 16, 2001, 427-431. --

Also in Other Publications, the following errors are corrected:

"Asoli, Hidetaka; Nishio, K.; Nakao, M.; Yokoo, A.; Tamaura, T.; Masuda, H., Fabrication of ideally ordered anodic porous alumina with 63 nm hole periodicity using sulfuric acid, J. Vac."

Should read

--Asoli, Hidetaka; Nishio, K.; Nakao, M.; Yokoo, A.; Tamaura, T.; Masuda, H., Fabrication of ideally ordered anodic porous alumina with 63 nm hole periodicity using sulfuric acid, J. Vac. Sci. Technol. B 19(2) Mar/April (2001) 569-572.--;

"Beauvais, Jacques; Lavallee, E.; Drouln, D.; Turcotte, D., Nano-Imprint Lithography Using Materials Fabricated by Sidwell Process, J. Vac. Sci. Technol. B, 17, 2957 (1999)."

Should read

--Beauvais, Jacques; Lavallee, E.; Drouin, D.; Turcotte, D., Nano-Imprint Lithography Using Materials Fabricated by Sidwell Process, J. Vac. Sci. Technol. B, 17, 2957 (1999).--;

"Berti, M,; Mazzi, G.; Calagnlle, L.; Drigo, A.V.; Merli, P.G.; Migliori, A., Composition and structure of Si-Ge layers produced by ion implantation and laser melting, J. Mater. Res., 6(10) Oct. 1991, 2120-2126."

Should read

--Berti, M.; Mazzi, G.; Calagnile, L; Drigo, A.V.; Merli, P.G.; Migliori, A., Composition and structure of Si-Ge layers produced by ion implantation and laser melting, J. Mater. Res., 6(10) Oct. 1991, 2120-2126.--; and

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"Xuan, Peiqi; Kectzierski, J.; Subranmanian, V.; Bokor, J.; King, T.-J., Hu, C., 60nm Planarized Ultra-thin Body Solid Phase Epitaxy MOSFETs, IEEE 58th DRC Meeting, Conf. Digest, Jun. 19-21, 2001, 67-68."

Should read

--Xuan, Peiqi; Kedzierski, J.; Subranmanian, V.; Bokor, J.; King, T.-J.; Hu, C., 60nm Planarized Ultra-thin Body Solid Phase Epitaxy MOSFETs, IEEE 58th DRC Meeting, Conf. Digest, Jun. 19-21, 2001, 67-68.--.

Column 8, line 24, "the to surface" should read --the surface--;

Column 8, line 58, "extend' should read --extent--; and

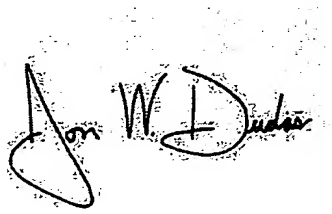
Column 9, line 11, "and been spaced" should read --and being spaced--.

In Claim 52, the following error is corrected:

Column 12, line 10, "being is" should read --being--.

Signed and Sealed this

Sixth Day of March, 2007



JON W. DUDAS
Director of the United States Patent and Trademark Office